

N-Channel Power MOSFET

600V, 2.3A, 4.4Ω

FEATURES

- 100% UIS and Rg tested
- Pb-free plating
- RoHS compliant
- Halogen-free according to IEC 61249-2-21

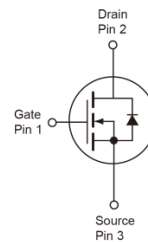
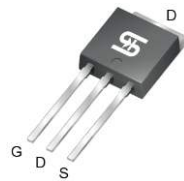
PRODUCT SUMMARY			
PARAMETER		VALUE	UNIT
V_{DS}		600	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	4.4	Ω
Q_g	$V_{GS} = 10V$	9.9	nC

APPLICATIONS

- Lighting
- Charger
- Power Supply
- Switching applications



TO-251 (IPAK)



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	2.3
		$T_C = 100^\circ\text{C}$	1.5
		$T_A = 25^\circ\text{C}$	0.4
Pulsed Drain Current ^(Note 1)	I_{DM}	9.2	A
Single Pulse Avalanche Current ^(Note 2)	I_{AS}	3.3	A
Single Pulse Avalanche Energy ^(Note 2)	E_{AS}	55	mJ
Total Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	60
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	°C

THERMAL RESISTANCE			
PARAMETER	SYMBOL	MAXIMUM	UNIT
Thermal Resistance – Junction to Case	$R_{\theta JC}$	2.1	°C/W
Thermal Resistance – Junction to Ambient	$R_{\theta JA}$	62	°C/W

Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	BV_{DSS}	600	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	2.5	2.9	4.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Drain-Source Leakage Current	$V_{GS} = 0\text{V}, V_{DS} = 600\text{V}$	I_{DSS}	--	--	10	μA
Drain-Source On-State Resistance (Note 3)	$V_{GS} = 10\text{V}, I_D = 1\text{A}$	$R_{DS(on)}$	--	3.9	4.4	Ω
Forward Transfer Conductance	$V_{DS} = 10\text{V}, I_D = 1\text{A}$	g_{fs}	--	2.8	--	S
Dynamic						
Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 480\text{V}, I_D = 2\text{A}$	Q_g	--	9.9	--	nC
Gate-Source Charge		Q_{gs}	--	1.5	--	
Gate-Drain Charge		Q_{gd}	--	4.7	--	
Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1.0\text{MHz}$	C_{iss}	--	316	--	pF
Output Capacitance		C_{oss}	--	32	--	
Reverse Transfer Capacitance		C_{rss}	--	1	--	
Gate Resistance	$f = 1.0\text{MHz}$	R_g	--	2.8	--	Ω
Switching (Note 4)						
Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 300\text{V}, I_D = 2\text{A}, R_G = 25\Omega$	$t_{d(on)}$	--	7.3	--	ns
Rise Time		t_r	--	9.6	--	
Turn-Off Delay Time		$t_{d(off)}$	--	23	--	
Fall Time		t_f	--	18	--	
Source-Drain Diode						
Diode Forward Voltage (Note 3)	$V_{GS} = 0\text{V}, I_S = 2\text{A}$	V_{SD}	--	0.8	1.4	V
Source Current	Integral reverse diode In the MOSFET	I_S	--	--	2.3	A
Source Current (Pulse)		I_{SM}	--	--	9.2	

Notes:

- Pulsed width limited by maximum junction temperature.
- $L = 10\text{mH}, V_{GS} = 10\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$.
- Pulse test: Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- Switching time is essentially independent of operating temperature.

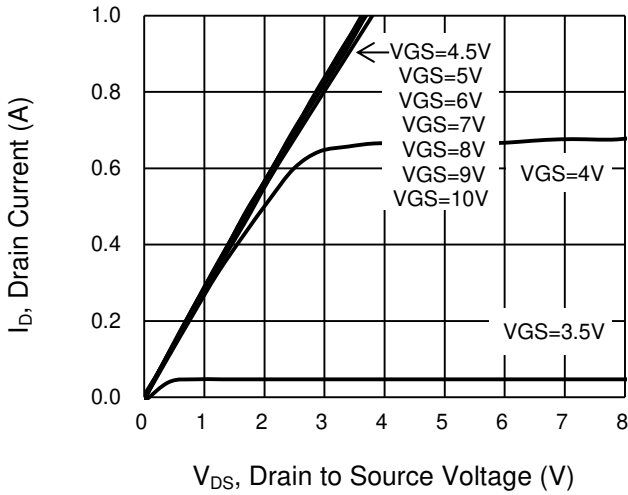
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM2NB60CH C5G	TO-251 (IPAK)	75 pcs / Tube

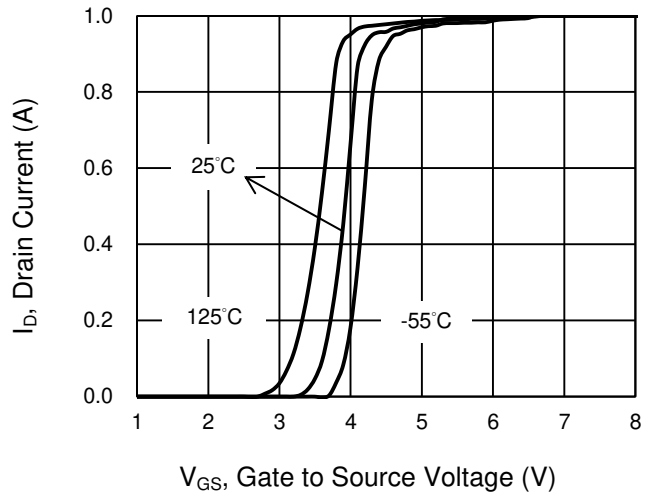
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

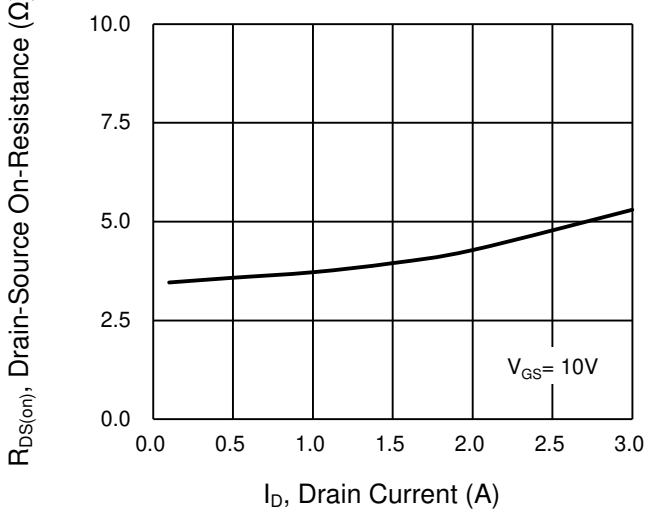
Output Characteristics



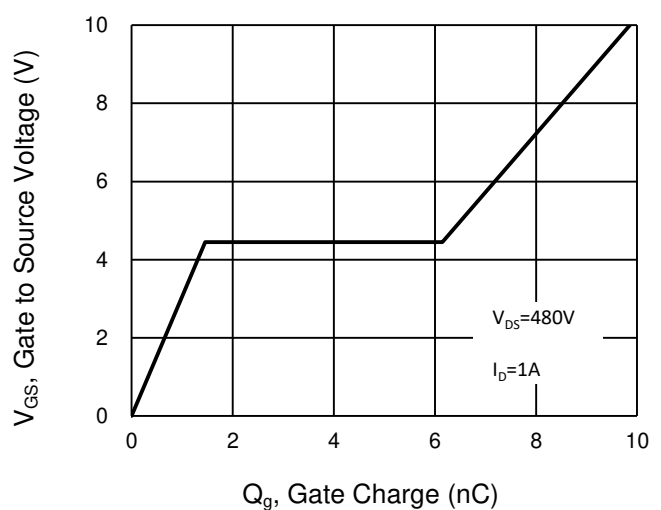
Transfer Characteristics



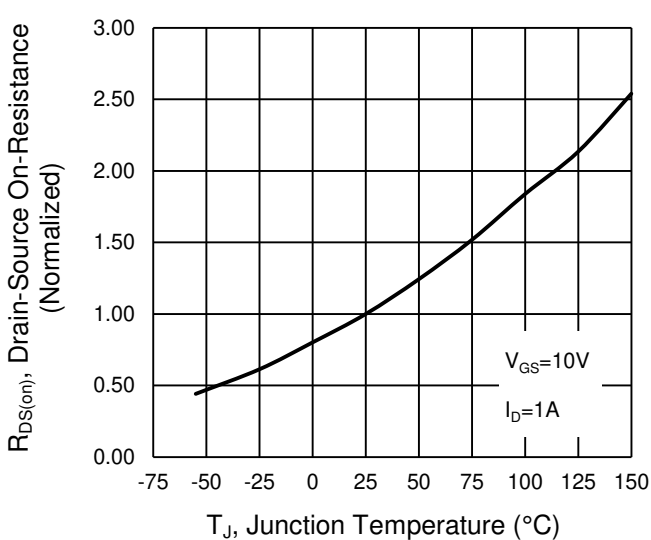
On-Resistance vs. Drain Current



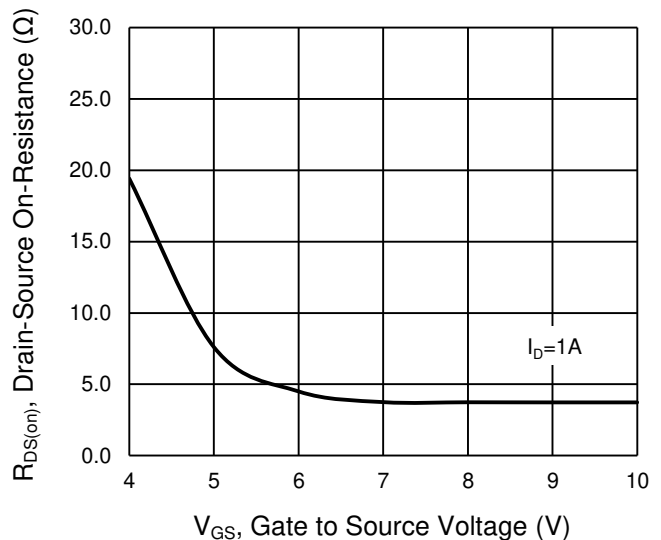
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



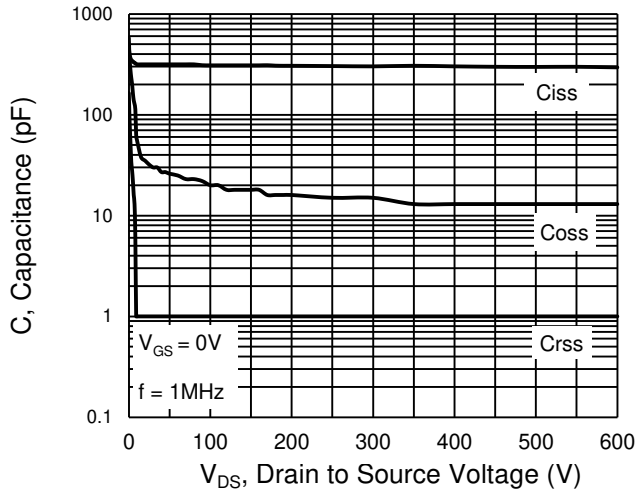
On-Resistance vs. Gate-Source Voltage



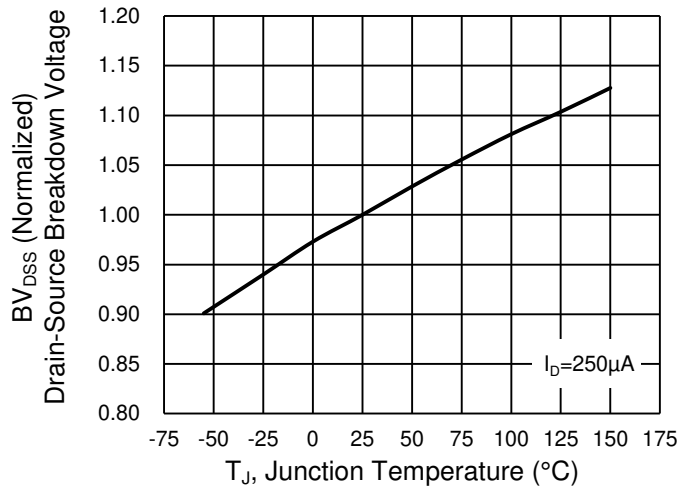
CHARACTERISTICS CURVES

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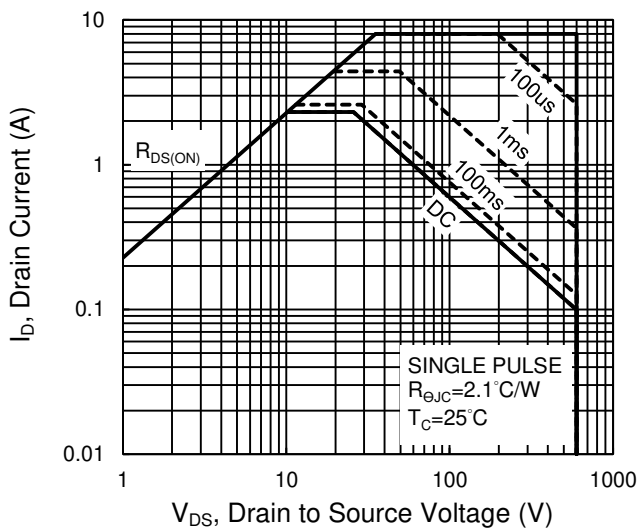
Capacitance vs. Drain-Source Voltage



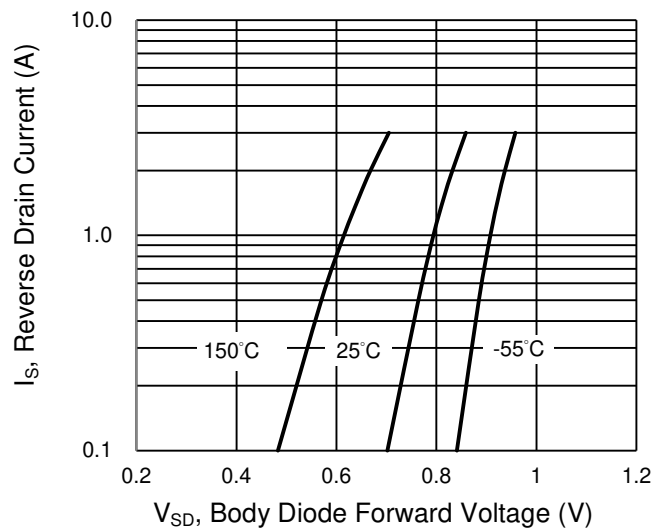
BV_{DSS} vs. Junction Temperature



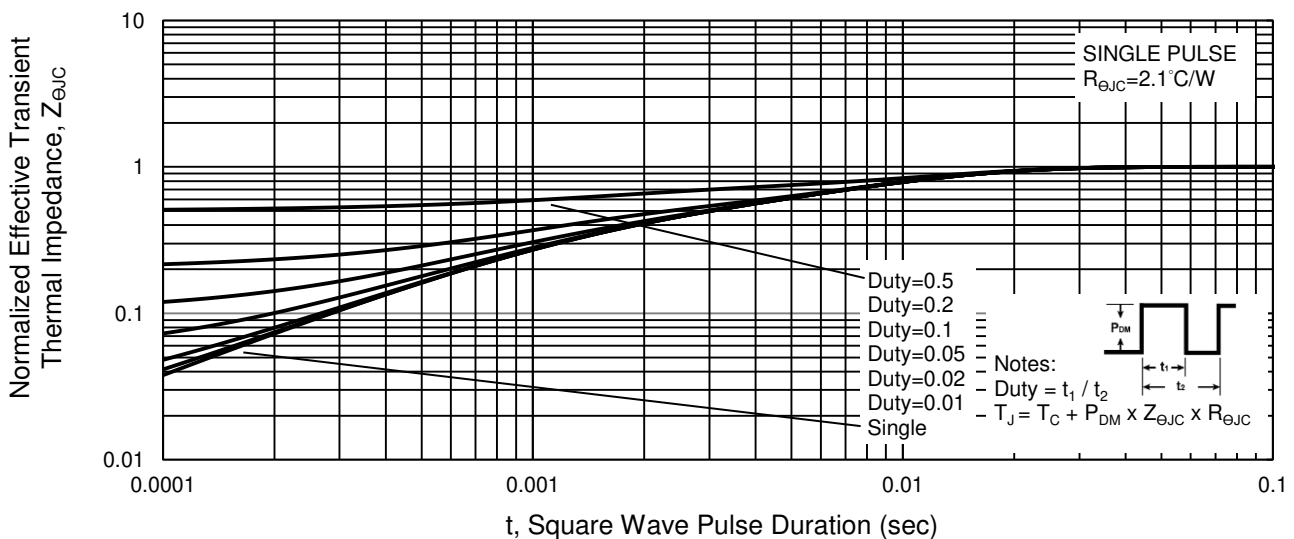
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage



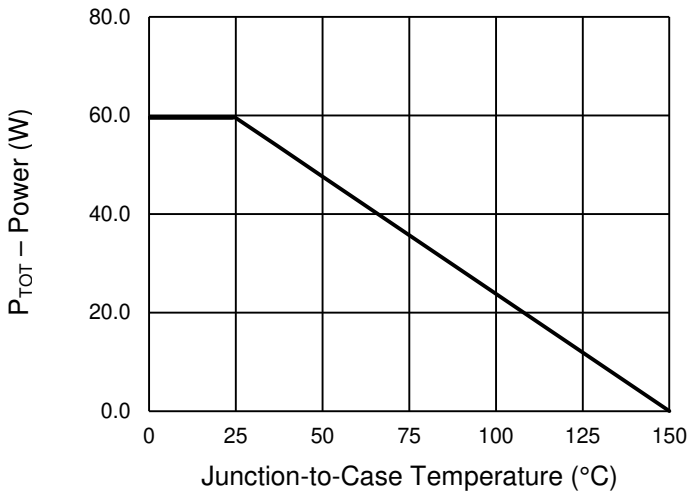
Normalized Thermal Transient Impedance, Junction-to-Case



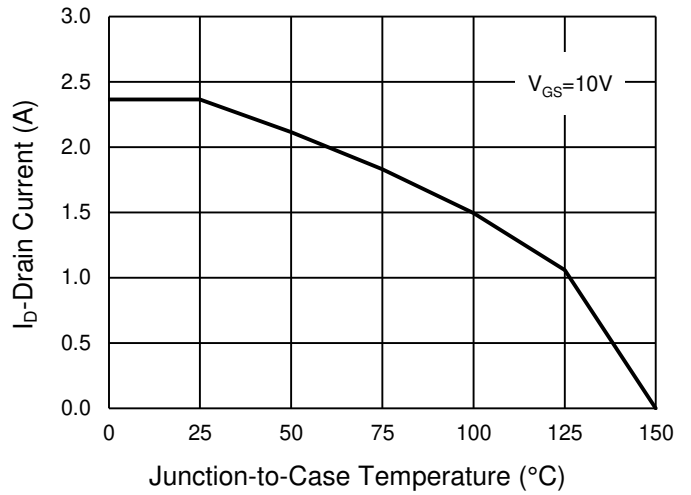
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

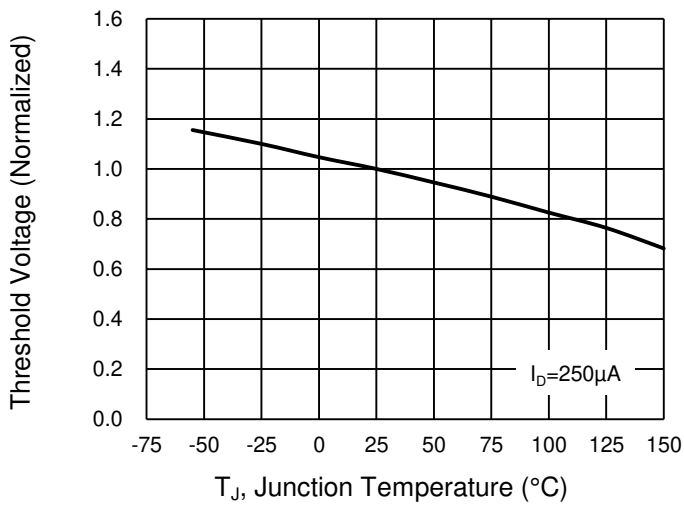
Power Dissipation



Drain Current

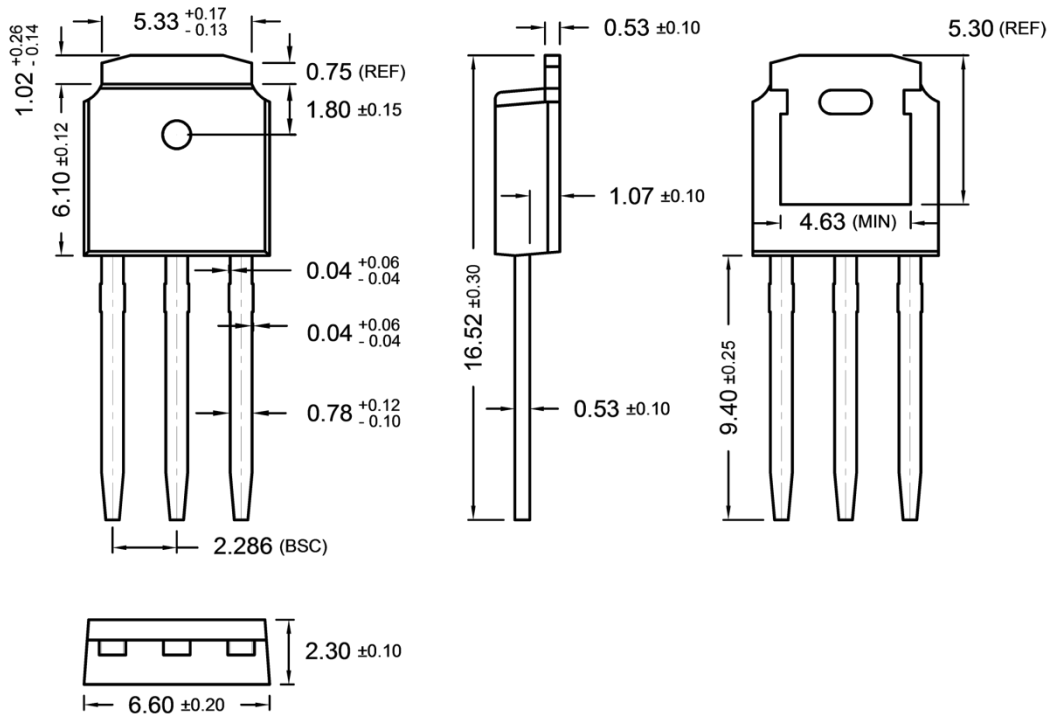


Normalized gate threshold voltage vs Temperature

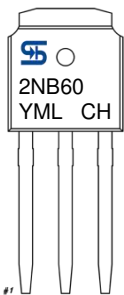


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

TO-251 (IPAK)



MARKING DIAGRAM



- Y** = Year Code
- M** = Month Code
 - O** =Jan **P** =Feb **Q** =Mar **R** =Apr
 - S** =May **T** =Jun **U** =Jul **V** =Aug
 - W** =Sep **X** =Oct **Y** =Nov **Z** =Dec
- L** = Lot Code (1~9, A~Z)

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